### SQD50N06-09L



Vishay Siliconix

# Automotive N-Channel 60 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY					
V <sub>DS</sub> (V)	60				
$R_{DS(on)}(\Omega)$ at $V_{GS}$ = 10 V	0.009				
$R_{DS(on)}(\Omega)$ at $V_{GS} = 4.5 V$	0.013				
I <sub>D</sub> (A)	50				
Configuration	Single				

# TO-252 G D S Top View N-Channel MOSFET

#### **FEATURES**

- Halogen-free According to IEC 61249-2-21
  Definition
- TrenchFET<sup>®</sup> Power MOSFET
- 100 % R<sub>g</sub> and UIS Tested
- Compliant to RoHS Directive 2002/95/EC
- AEC-Q101 Qualified<sup>d</sup>



ORDERING INFORMATION	
Package	TO-252
Lead (Pb)-free and Halogen-free	SQD50N06-09L-GE3

<b>ABSOLUTE MAXIMUM RATINGS</b> ( $T_C = 25$ °C, unless otherwise noted)					
PARAMETER	SYMBOL	LIMIT	UNIT		
Drain-Source Voltage		V <sub>DS</sub>	60	N/	
Gate-Source Voltage		V <sub>GS</sub>	± 20	V	
Continuous Drain Current	$T_C = 25 \ ^{\circ}C^a$	1	50		
Continuous Drain Current	T <sub>C</sub> = 125 °C	l I <sub>D</sub>	49		
Continuous Source Current (Diode Conduction) <sup>a</sup>		I <sub>S</sub>	50	А	
Pulsed Drain Current <sup>b</sup>		I <sub>DM</sub>	200		
Single Pulse Avalanche Energy	L = 0.1 mH	I <sub>AS</sub>	48		
Single Pulse Avalanche Current		E <sub>AS</sub>	115	mJ	
Marian Davier Diasia Aliand	T <sub>C</sub> = 25 °C	р	136	w	
Maximum Power Dissipation <sup>b</sup>	T <sub>C</sub> = 125 °C	P <sub>D</sub>	45		
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	- 55 to + 175	°C	

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-Ambient	PCB Mount <sup>c</sup>	R <sub>thJA</sub>	50	°C/W
Junction-to-Case (Drain)		R <sub>thJC</sub>	1.1	0/10

#### Notes

- a. Package limited.
- b. Pulse test; pulse width  $\leq 300~\mu s,~duty~cycle \leq 2~\%.$
- c. When mounted on 1" square PCB (FR-4 material).
- d. Parametric verification ongoing.

S11-2065-Rev. B, 24-Oct-11

1

SQD50N06-09L



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PARAMETER	SYMBOL	TES	TEST CONDITIONS		TYP.	MAX.	UNIT	
Static					•			
Drain-Source Breakdown Voltage	V <sub>DS</sub>	$V_{GS} = 0 V, I_D = 250 \mu A$		60	-	-	v	
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	$V_{DS} = V_{GS}$ , $I_D = 250 \ \mu A$		2.0	2.5	v	
Gate-Source Leakage	I <sub>GSS</sub>	V <sub>DS</sub> =	$V_{DS} = 0 V, V_{GS} = \pm 20 V$		-	± 100	nA	
		$V_{GS} = 0 V$	V <sub>DS</sub> = 60 V	-	-	1.0		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{GS} = 0 V$	V <sub>DS</sub> = 60 V, T <sub>J</sub> = 125 °C	-	-	50	μA	
		$V_{GS} = 0 V$	V <sub>DS</sub> = 60 V, T <sub>J</sub> = 175 °C	-	-	250		
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{GS} = 10 V$	$V_{DS} \ge 5 V$	50	-	-	Α	
		$V_{GS} = 10 V$	I <sub>D</sub> = 20 A	-	0.0071	0.0090	Ω	
	5	$V_{GS} = 10 V$	I <sub>D</sub> = 20 A, T <sub>J</sub> = 125 °C	-	-	0.016		
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 20 A, T <sub>J</sub> = 175 °C	-	-	0.019		
		$V_{GS} = 4.5 V$	I <sub>D</sub> = 10 A	-	0.0094	0.013		
Forward Transconductanceb	g <sub>fs</sub>	V <sub>DS</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 20 A		62	-	S	
Dynamic <sup>b</sup>					•			
Input Capacitance	C <sub>iss</sub>		/ V <sub>DS</sub> = 25 V, f = 1 MHz	-	2451	3065	pF	
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0 V$		-	435	545		
Reverse Transfer Capacitance	C <sub>rss</sub>			-	192	240		
Total Gate Charge <sup>c</sup>	Qg			-	48	72	nC	
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>	V <sub>GS</sub> = 10 V	$V_{DS} = 30 \text{ V}, I_D = 50 \text{ A}$	-	7.1	-		
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>			-	13.5	-		
Gate Resistance	Rg	f = 1 MHz		0.85	1.7	2.6	Ω	
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>			-	10	15		
Rise Time <sup>c</sup>	t <sub>r</sub>	$\label{eq:VDD} \begin{array}{l} V_{\text{DD}} = 30 \text{ V}, \ R_{\text{L}} = 0.6 \ \Omega \\ I_{\text{D}} \cong 50 \text{ A}, \ V_{\text{GEN}} = 10 \text{ V}, \ R_{\text{g}} = 1 \ \Omega \end{array}$		-	11	17	ns	
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>			-	27	41		
Fall Time <sup>c</sup>	t <sub>f</sub>			-	8	12		
Source-Drain Diode Ratings and Char	acteristics <sup>b</sup>							
Pulsed Current <sup>a</sup>	I <sub>SM</sub>	1		-	-	200	А	
Forward Voltage	V <sub>SD</sub>	$I_{\rm F} = 20 \text{ A}, V_{\rm GS} = 0 \text{ V}$		-	0.82	1.5	V	

Notes

a. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %.

b. Guaranteed by design, not subject to production testing.

c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



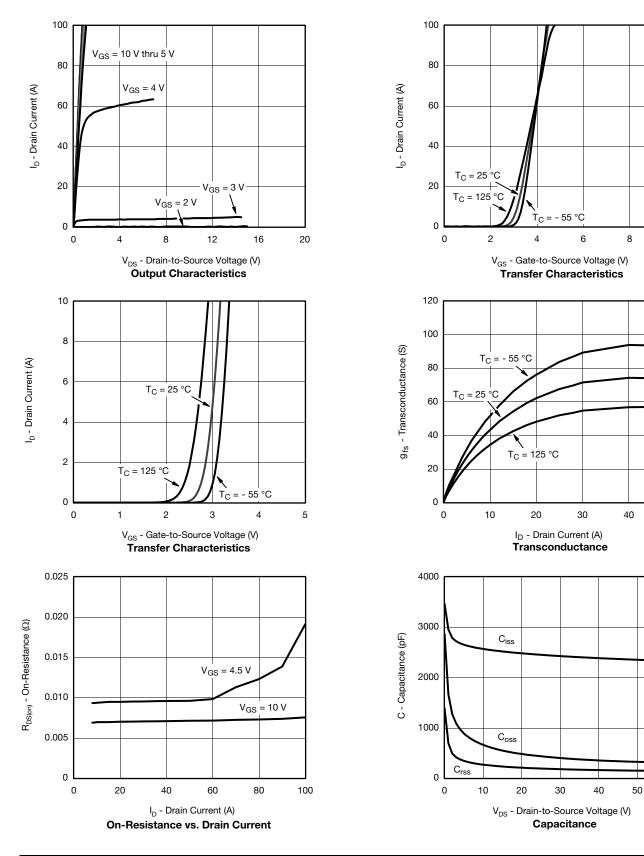
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#### **TYPICAL CHARACTERISTICS** ( $T_A = 25 \text{ °C}$ , unless otherwise noted)



S11-2065-Rev. B, 24-Oct-11

3

Document Number: 68901

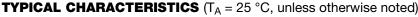
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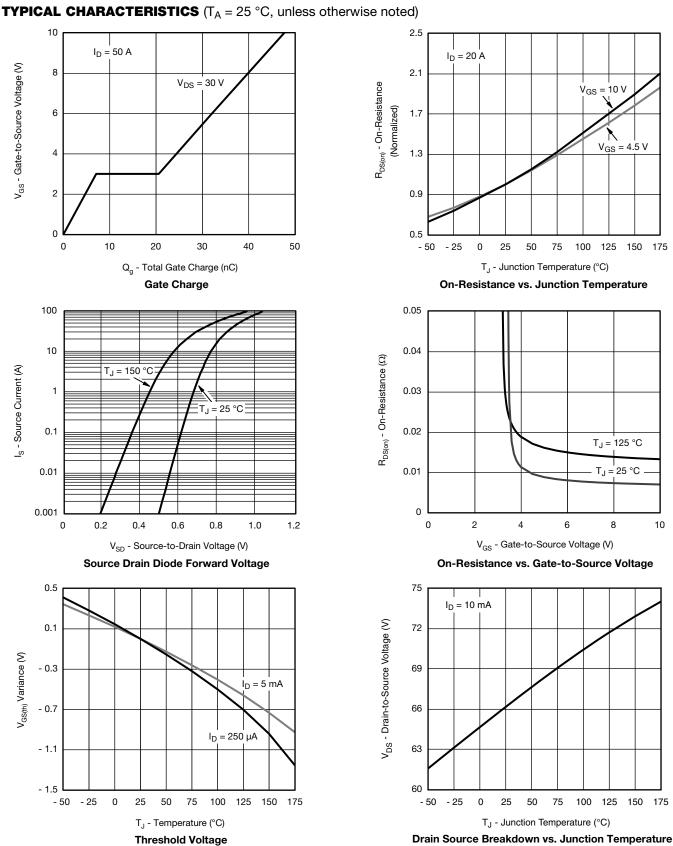
S11-2065-Rev. B, 24-Oct-11

4

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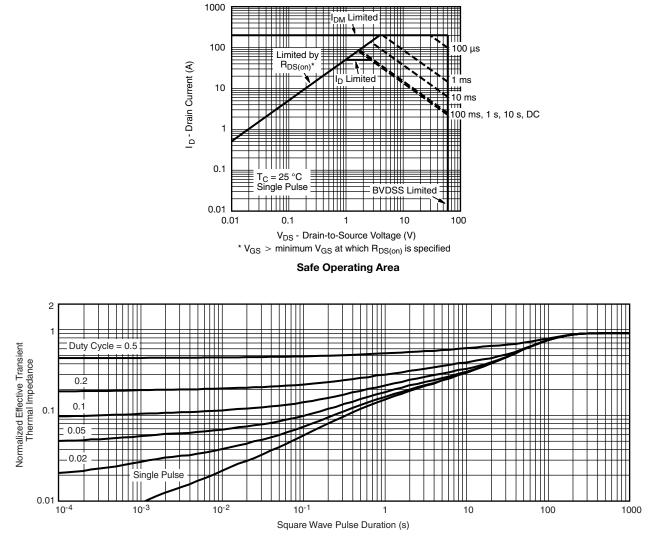
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#### **THERMAL RATINGS** ( $T_A = 25 \text{ °C}$ , unless otherwise noted)

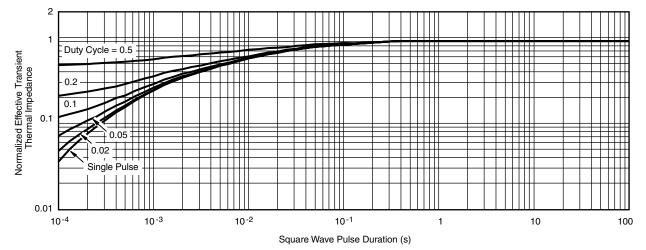


Normalized Thermal Transient Impedance, Junction-to-Ambient



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#### **THERMAL RATINGS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

#### Note

• The characteristics shown in the two graphs

- Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)

- Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

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Е b3 Ľ Δ ŝ b2 e1 Б E1

# C2 т gage plane height (0.5 mm)

-C

- A1

**TO-252AA** Case Outline

	MILLIN	<b>IETERS</b>	INCHES		
DIM.	MIN.	MAX.	MIN.	MAX.	
А	2.18	2.38	0.086	0.094	
A1	-	0.127	-	0.005	
b	0.64	0.88	0.025	0.035	
b2	0.76	1.14	0.030	0.045	
b3	4.95	5.46	0.195	0.215	
С	0.46	0.61	0.018	0.024	
C2	0.46	0.89	0.018	0.035	
D	5.97	6.22	0.235	0.245	
D1	4.10	-	0.161	-	
Е	6.35	6.73	0.250	0.265	
E1	4.32	-	0.170	-	
Н	9.40	10.41	0.370	0.410	
е	2.28 BSC 0.090 BSC				
e1	4.56 BSC		0.180 BSC		
L	1.40	1.78	0.055	0.070	
L3	0.89	1.27	0.035	0.050	
L4	-	1.02	-	0.040	
L5	1.01	1.52	0.040	0.060	
ECN: T13-0592-Rev. A, 02-Sep-13 DWG: 6019					

Note

• Dimension L3 is for reference only.





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#### **RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)**



Recommended Minimum Pads Dimensions in Inches/(mm)

Return to Index



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